

SKT 491, SKT 551

V_{RSM}	V_{RRM}	$(dv/dt)_{cr}$	I_{TRMS} (maximum values for continuous operation)	
			1000 A	1200 A
V	V	$V/\mu s$	I_{TAV} (sin. 180; $T_{case} = \dots$; DSC)	
500	400	1000	SKT 491/04 E	—
900	800	1000	SKT 491/08 E	SKT 551/08 E
1300	1200	1000	SKT 491/12 E	SKT 551/12 E
1500	1400	1000	SKT 491/14 E	SKT 551/14 E
1700	1600	1000	SKT 491/16 E	SKT 551/16 E
1900	1800	1000	SKT 491/18 E	SKT 551/18 E

Thyristors

SKT 491

SKT 551



Symbol	Conditions	SKT 491	SKT 551	Units
I_{TAV}	sin. 180; ($T_{case} = \dots$); DSC	490 (80)	550 (85)	A °C
I_{TSM}	$T_{vj} = 25^\circ C$	8 000	9 000	A
i^2t	$T_{vj} = 125^\circ C$	7 000	8 000	A
	$T_{vj} = 25^\circ C$	320 000	405 000	A^2s
	$T_{vj} = 125^\circ C$	245 000	320 000	A^2s
t_{gd}	$T_{vj} = 25^\circ C$	typ. 1		μs
t_{gr}	$I_G = 1 A$ $di_G/dt = 1 A/\mu s$			
$(di/dt)_{cr}$	$V_D = 0,67 \cdot V_{DRM}$	typ. 1		μs
I_H	$f = 50 \dots 60 Hz$	125		μs
I_L	$T_{vj} = 25^\circ C$; typ./max.	150 / 500		A/ μs
t_q	$T_{vj} = 25^\circ C$; $R_G = 33 \Omega$; typ./max.	0,5 / 2		mA
	$T_{vj} = 125^\circ C$; typ.	50 ... 150		A
V_T	$T_{vj} = 25^\circ C$; $I_T = 1500 A$; max.	2,1	1,65	μs
$V_{T(TO)}$	$T_{vj} = 125^\circ C$	1,1	0,925	V
r_T	$T_{vj} = 125^\circ C$	0,7	0,45	$m\Omega$
$I_{DD}; I_{RD}$	$T_{vj} = 125^\circ C$; $V_{RD} = V_{RRM}$ $V_{DD} = V_{DRM}$	50		mA
V_{GT}	$T_{vj} = 25^\circ C$	3		V
I_{GT}	$T_{vj} = 25^\circ C$	250		mA
V_{GD}	$T_{vj} = 125^\circ C$	0,25		V
I_{GD}	$T_{vj} = 125^\circ C$	10		mA
R_{thjc}	cont.; sin. 180; DSC/SSC	0,045		$^\circ C/W$
	rec. 120; DSC/SSC	0,047 / 0,100		$^\circ C/W$
	DSC/SSC	0,054 / 0,113		$^\circ C/W$
R_{thch}		0,012 / 0,024		$^\circ C/W$
T_{vj}		– 40 ... + 125		°C
T_{stg}		– 40 ... + 130		°C
F	SI units	5,2 ... 8		kN
w	US units	1200 ... 1800		lbs.
Case	→ page B 3 – 32	105		g
		B 11		

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.

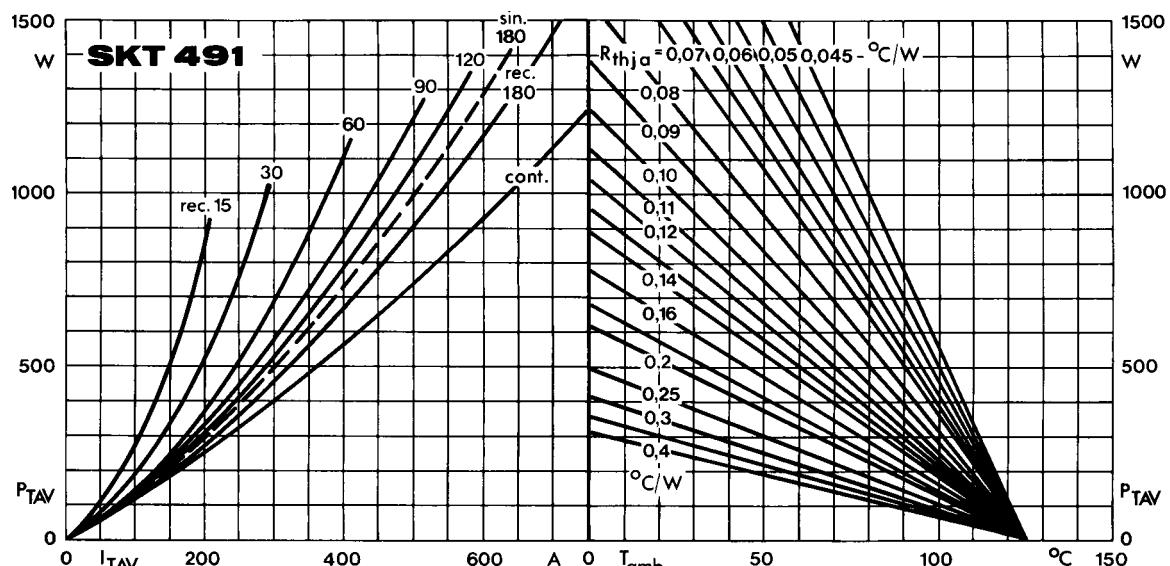


Fig. 1 a Power dissipation vs. on-state current and ambient temperature

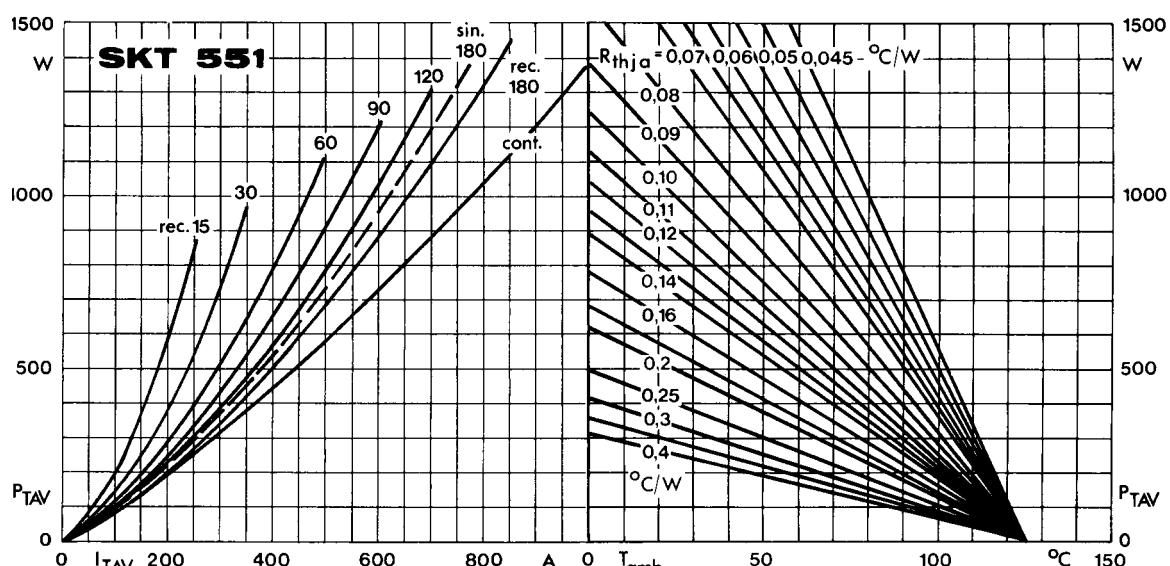


Fig. 1 b Power dissipation vs. on-state current and ambient temperature

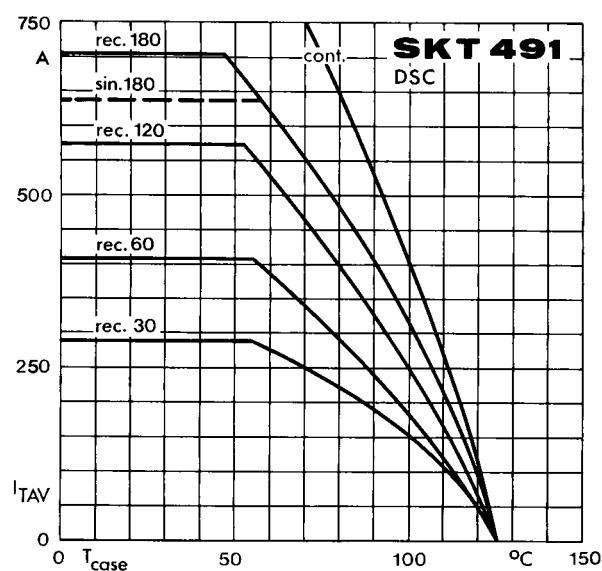


Fig. 2 a Rated on-state current vs. case temperature

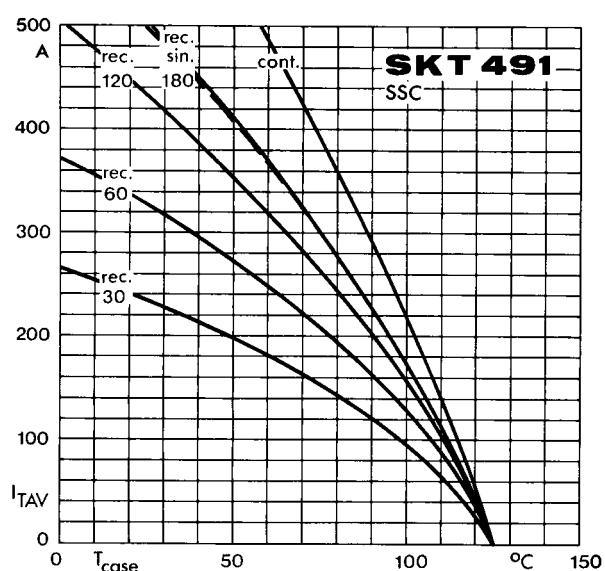


Fig. 2 b Rated on-state current vs. case temperature

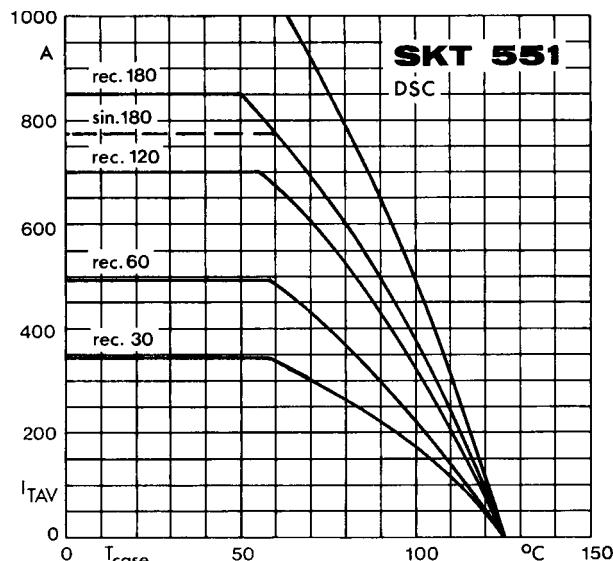


Fig. 2 c Rated on-state current vs. case temperature

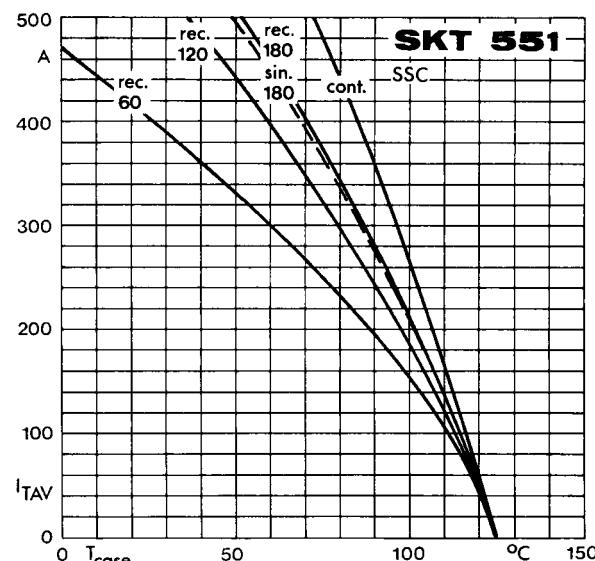


Fig. 2 d Rated on-state current vs. case temperature

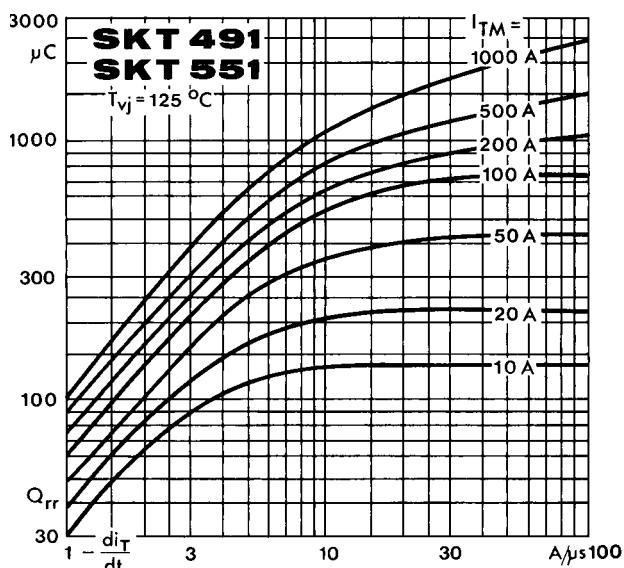


Fig. 3 Recovered charge vs. current decrease

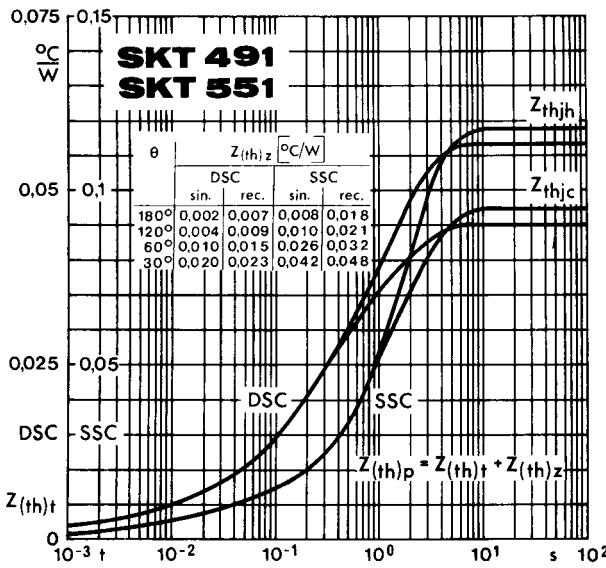


Fig. 4 Transient thermal impedance vs. time

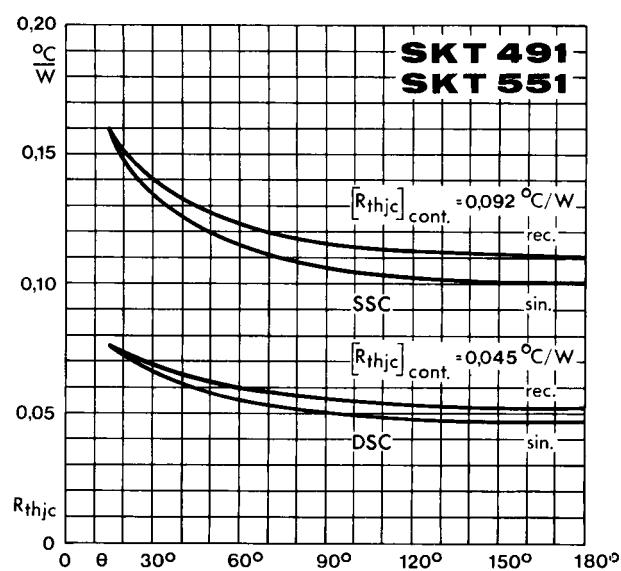


Fig. 5 Thermal resistance vs. conduction angle

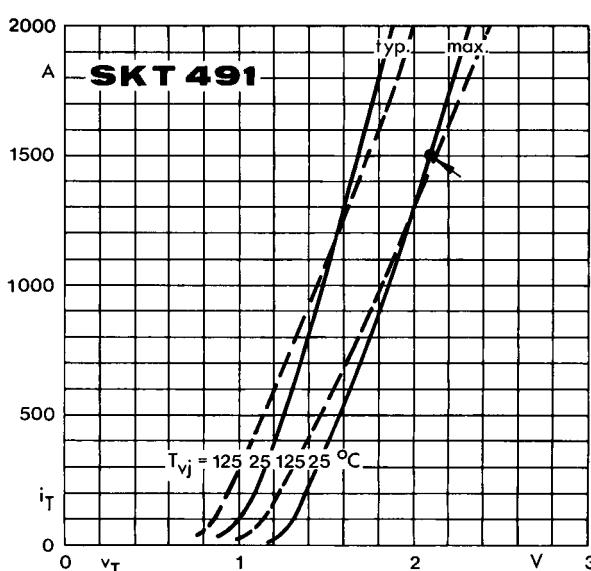


Fig. 6 a On-state characteristics

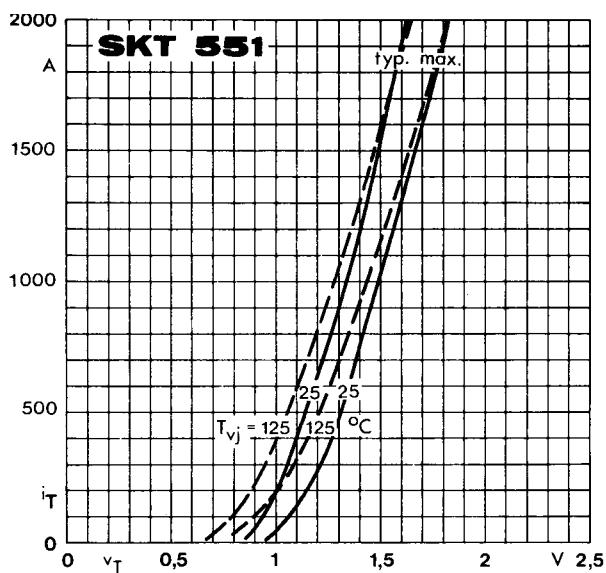


Fig. 6 b On-state characteristics

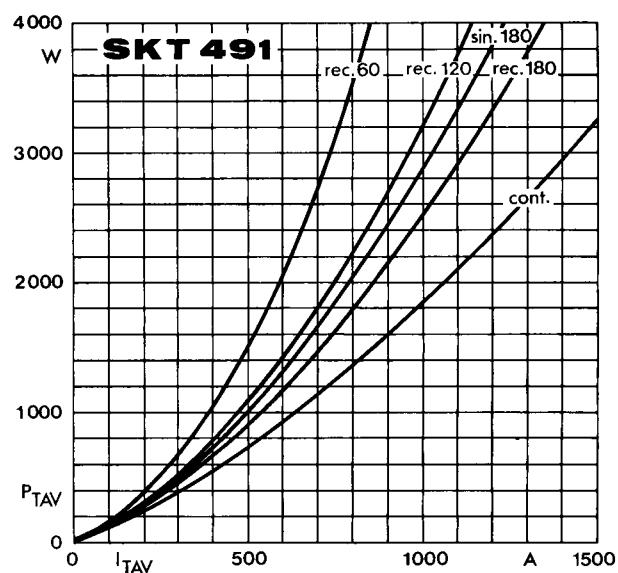


Fig. 7 a Power dissipation vs. on-state current

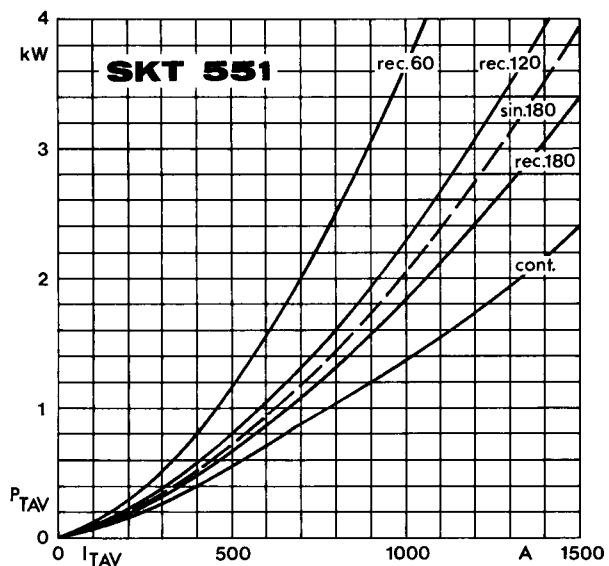


Fig. 7 b Power dissipation vs. on-state current

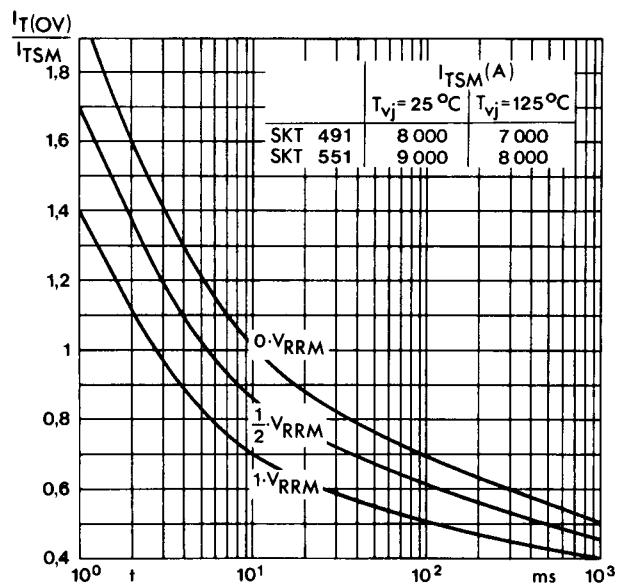


Fig. 8 Surge overload current vs. time

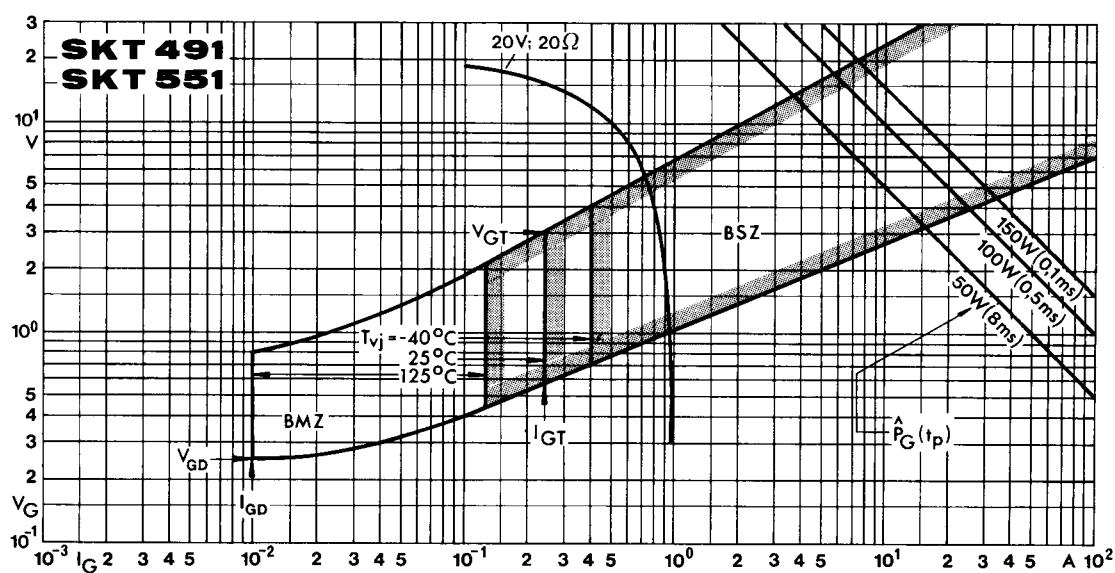
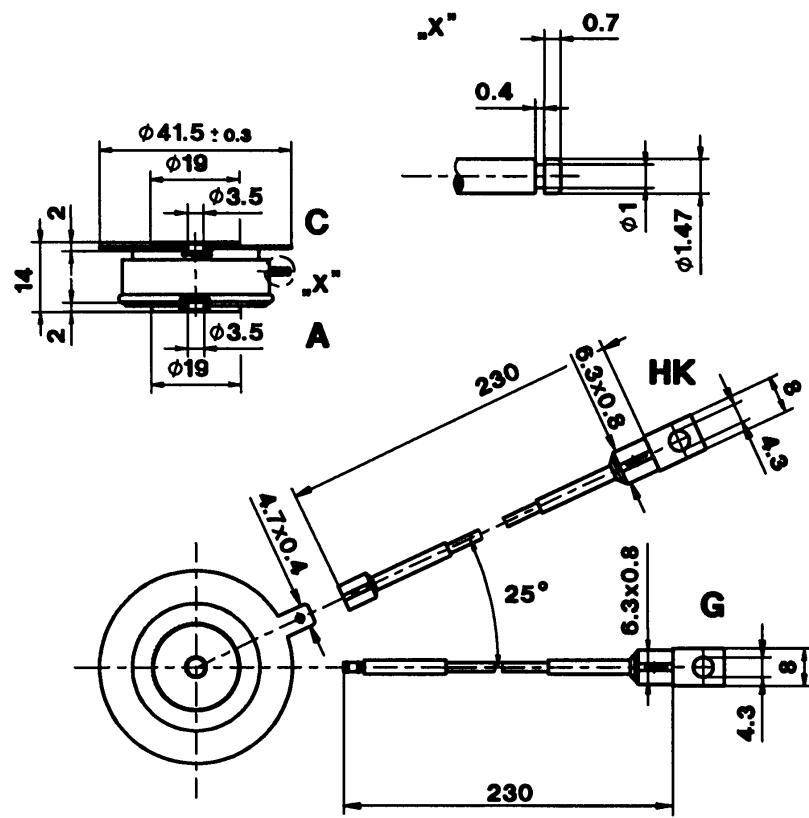


Fig. 9 Gate trigger characteristics

SKT 240
SKT 340

Case B 8

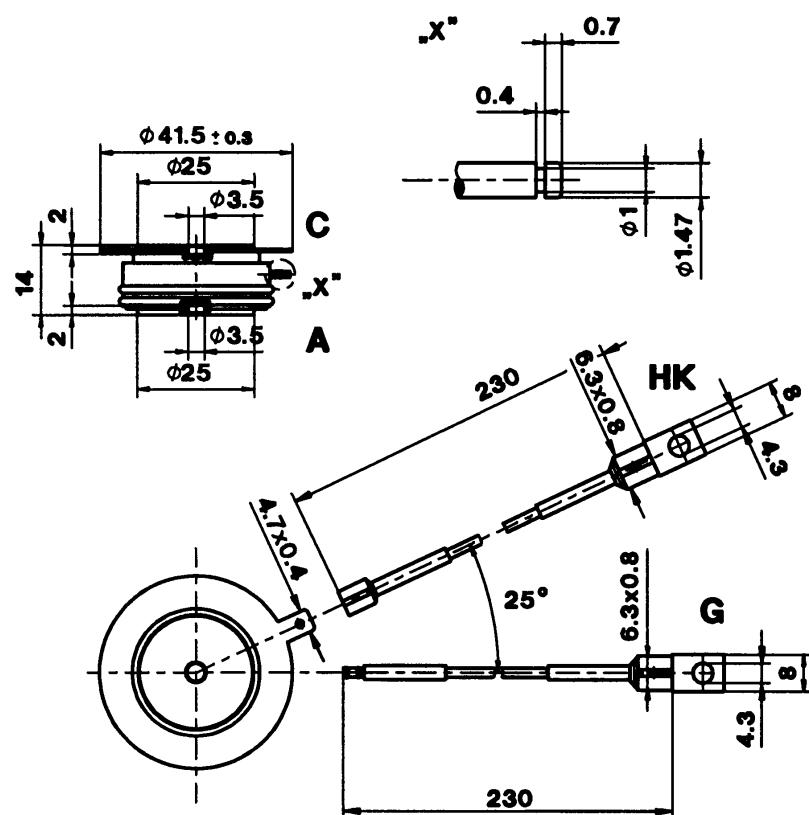
DIN 41814: 151 A 4
JEDEC: TO-200 AB



SKT 491
SKT 551

Case B 11

DIN 41814: 152 A 4
JEDEC: TO-200 AB



C: Cathode terminal (red sleeve)

A: Anode terminal

G: Gate terminal (yellow sleeve)

HK: Auxiliary cathode terminal (red sleeve)

Dimensions in mm